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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I²C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	79
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	24K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 28x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/spc560b40l3b6e0x

2 Block diagram

Figure 1 shows a top-level block diagram of the SPC560B40x/50x and SPC560C40x/50x device series.

Table 3. SPC560B40x/50x and SPC560C40x/50x series block summary (continued)

Block	Function
Memory protection unit (MPU)	Provides hardware access control for all memory references generated in a device
Nexus development interface (NDI)	Provides real-time development support capabilities in compliance with the IEEE-ISTO 5001-2003 standard
Periodic interrupt timer (PIT)	Produces periodic interrupts and triggers
Real-time counter (RTC)	A free running counter used for time keeping applications, the RTC can be configured to generate an interrupt at a predefined interval independent of the mode of operation (run mode or low-power mode)
System integration unit (SIU)	Provides control over all the electrical pad controls and up 32 ports with 16 bits of bidirectional, general-purpose input and output signals and supports up to 32 external interrupts with trigger event configuration
Static random-access memory (SRAM)	Provides storage for program code, constants, and variables
System status configuration module (SSCM)	Provides system configuration and status data (such as memory size and status, device mode and security status), device identification data, debug status port enable and selection, and bus and peripheral abort enable/disable
System timer module (STM)	Provides a set of output compare events to support AUTOSAR (Automotive Open System Architecture) and operating system tasks
Software watchdog timer (SWT)	Provides protection from runaway code
Wakeup unit (WKPU)	The wakeup unit supports up to 18 external sources that can generate interrupts or wakeup events, of which 1 can cause non-maskable interrupt requests or wakeup events.
Crossbar (XBAR) switch	Supports simultaneous connections between two master ports and three slave ports. The crossbar supports a 32-bit address bus width and a 64-bit data bus width.

3.3 Voltage supply pins

Voltage supply pins are used to provide power to the device. Three dedicated VDD_LV/VSS_LV supply pairs are used for 1.2 V regulator stabilization.

Table 4. Voltage supply pin descriptions

Port pin	Function	Pin number			
		LQFP64	LQFP100	LQFP144	LBGA208[(1)]
VDD_HV	Digital supply voltage	7, 28, 56	15, 37, 70, 84	19, 51, 100, 123	C2, D9, E16, G13, H3, N9, R5
VSS_HV	Digital ground	6, 8, 26, 55	14, 16, 35, 69, 83	18, 20, 49, 99, 122	G7, G8, G9, G10, H1, H7, H8, H9, H10, J7, J8, J9, J10, K7, K8, K9, K10
VDD_LV	1.2V decoupling pins. Decoupling capacitor must be connected between these pins and the nearest V_{SS_LV} pin.[(2)]	11, 23, 57	19, 32, 85	23, 46, 124	D8, K4, P7
VSS_LV	1.2V decoupling pins. Decoupling capacitor must be connected between these pins and the nearest V_{DD_LV} pin.[(2)]	10, 24, 58	18, 33, 86	22, 47, 125	C8, J2, N7
VDD_BV	Internal regulator supply voltage	12	20	24	K3
VSS_HV_ADC	Reference ground and analog ground for the ADC	33	51	73	R15
VDD_HV_ADC	Reference voltage and analog supply for the ADC	34	52	74	P14

1. LBGA208 available only as development package for Nexus2+
2. A decoupling capacitor must be placed between each of the three VDD_LV/VSS_LV supply pairs to ensure stable voltage (see the recommended operating conditions in the device datasheet for details).

3.4 Pad types

In the device the following types of pads are available for system pins and functional port pins:

S = Slow[(b)]

M = Medium[(b) (c)]

F = Fast[(b) (c)]

I = Input only with analog feature[(b)]

J = Input/Output (‘S’ pad) with analog feature

X = Oscillator

b. See the I/O pad electrical characteristics in the device datasheet for details.

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function(1)	Function	Peripheral	I/O direction(2)	Pad type	RESET configuration	Pin number LQFP64	Pin number LQFP100	Pin number LQFP144	Pin number LBGA208(3)
PC[15]	PCR[47]	AF0 AF1 AF2 AF3	GPIO[47] E0UC[15] CS0_2 —	SIUL eMIOS_0 DSPI_2 —	I/O I/O I/O —	M	Tristate	—	4	4	D3
PD[0]	PCR[48]	AF0 AF1 AF2 AF3 —	GPIO[48] — — — GPI[4]	SIUL — — — ADC	I — — — I	I	Tristate	—	41	63	P12
PD[1]	PCR[49]	AF0 AF1 AF2 AF3 —	GPIO[49] — — — GPI[5]	SIUL — — — ADC	I — — — I	I	Tristate	—	42	64	T12
PD[2]	PCR[50]	AF0 AF1 AF2 AF3 —	GPIO[50] — — — GPI[6]	SIUL — — — ADC	I — — — I	I	Tristate	—	43	65	R12
PD[3]	PCR[51]	AF0 AF1 AF2 AF3 —	GPIO[51] — — — GPI[7]	SIUL — — — ADC	I — — — I	I	Tristate	—	44	66	P13
PD[4]	PCR[52]	AF0 AF1 AF2 AF3 —	GPIO[52] — — — GPI[8]	SIUL — — — ADC	I — — — I	I	Tristate	—	45	67	R13
PD[5]	PCR[53]	AF0 AF1 AF2 AF3 —	GPIO[53] — — — GPI[9]	SIUL — — — ADC	I — — — I	I	Tristate	—	46	68	T13

Table 6. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function(1)	Function	Peripheral	I/O direction(2)	Pad type	RESET configuration	Pin number			
								LQFP64	LQFP100	LQFP144	LBGA208(3)
PD[13]	PCR[61]	AF0 AF1 AF2 AF3 —	GPIO[61] CS0_1 E0UC[25] — ANS[5]	SIUL DSPI_1 eMIOS_0 — ADC	I/O I/O I/O — I	J	Tristate	—	62	84	M14
PD[14]	PCR[62]	AF0 AF1 AF2 AF3 —	GPIO[62] CS1_1 E0UC[26] — ANS[6]	SIUL DSPI_1 eMIOS_0 — ADC	I/O O I/O — I	J	Tristate	—	64	86	L15
PD[15]	PCR[63]	AF0 AF1 AF2 AF3 —	GPIO[63] CS2_1 E0UC[27] — ANS[7]	SIUL DSPI_1 eMIOS_0 — ADC	I/O O I/O — I	J	Tristate	—	66	88	L14
PE[0]	PCR[64]	AF0 AF1 AF2 AF3 — —	GPIO[64] E0UC[16] — — CAN5RX(11) WKPU[6](4)	SIUL eMIOS_0 — — FlexCAN_5 WKPU	I/O I/O — — I I	S	Tristate	—	6	10	F1
PE[1]	PCR[65]	AF0 AF1 AF2 AF3	GPIO[65] E0UC[17] CAN5TX(11) —	SIUL eMIOS_0 FlexCAN_5 —	I/O I/O O —	M	Tristate	—	8	12	F4
PE[2]	PCR[66]	AF0 AF1 AF2 AF3 —	GPIO[66] E0UC[18] — — SIN_1	SIUL eMIOS_0 — — DSPI_1	I/O I/O — — I	M	Tristate	—	89	128	D7
PE[3]	PCR[67]	AF0 AF1 AF2 AF3	GPIO[67] E0UC[19] SOUT_1 —	SIUL eMIOS_0 DSPI_1 —	I/O I/O O —	M	Tristate	—	90	129	C7

Table 14. Recommended operating conditions (5.0 V) (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–5	5	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	mA
TV_{DD}	SR	V_{DD} slope to ensure correct power up(6)	—	3.0(7)	250×10^3 (0.25 [V/µs])	V/s

1. 100 nF capacitance needs to be provided between each V_{DD}/V_{SS} pair.
2. Full device operation is guaranteed by design when the voltage drops below 4.5 V down to 3.0 V. However, certain analog electrical characteristics will not be guaranteed to stay within the stated limits.
3. 330 nF capacitance needs to be provided between each V_{DD_LV}/V_{SS_LV} supply pair.
4. 100 nF capacitance needs to be provided between V_{DD_BV} and the nearest V_{SS_LV} (higher value may be needed depending on external regulator characteristics).
5. 1 µF (electrolithic/tantalum) + 47 nF (ceramic) capacitance needs to be provided between V_{DD_ADC}/V_{SS_ADC} pair. Another ceramic cap of 10 nF with low inductance package can be added.
6. Guaranteed by device validation.
7. Minimum value of TV_{DD} must be guaranteed until V_{DD} reaches 2.6 V (maximum value of V_{PORH}).

Note: RAM data retention is guaranteed with V_{DD_LV} not below 1.08 V.

3.14 Thermal characteristics

3.14.1 Package thermal characteristics

Table 15. LQFP thermal characteristics(1)

Symbol		C	Parameter	Conditions(2)	Pin count	Value	Unit
$R_{\theta JA}$	CC	D	Thermal resistance, junction-to-ambient natural convection(3)	Single-layer board - 1s	64	60	°C/W
					100	64	
					144	64	
				Four-layer board - 2s2p	64	42	
					100	51	
					144	49	
$R_{\theta JB}$	CC	D	Thermal resistance, junction-to-board(4)	Single-layer board - 1s	64	24	°C/W
					100	36	
					144	37	
				Four-layer board - 2s2p	64	24	
					100	34	
					144	35	

Most of the time for the applications, $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant, if the device is configured to continuously drive external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

Equation 2 $P_D = K / (T_J + 273\ °C)$

Therefore, solving equations *Equation 1* and *Equation 2*:

Equation 3 $K = P_D \times (T_A + 273\ °C) + R_{\theta JA} \times P_D^2$

Where:

K is a constant for the particular part, which may be determined from *Equation 3* by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J may be obtained by solving equations *Equation 1* and *Equation 2* iteratively for any value of T_A.

3.15 I/O pad electrical characteristics

3.15.1 I/O pad types

The device provides four main I/O pad types depending on the associated alternate functions:

- Slow pads—These pads are the most common pads, providing a good compromise between transition time and low electromagnetic emission.
- Medium pads—These pads provide transition fast enough for the serial communication channels with controlled current to reduce electromagnetic emission.
- Fast pads—These pads provide maximum speed. There are used for improved Nexus debugging capability.
- Input only pads—These pads are associated to ADC channels and the external 32 kHz crystal oscillator (SXOSC) providing low input leakage.

Medium and Fast pads can use slow configuration to reduce electromagnetic emission, at the cost of reducing AC performance.

3.15.2 I/O input DC characteristics

Table 16 provides input DC electrical characteristics as described in *Figure 6*.

3.15.3 I/O output DC characteristics

The following tables provide DC characteristics for bidirectional pads:

- *Table 17* provides weak pull figures. Both pull-up and pull-down resistances are supported.
- *Table 18* provides output driver characteristics for I/O pads when in SLOW configuration.
- *Table 19* provides output driver characteristics for I/O pads when in MEDIUM configuration.
- *Table 20* provides output driver characteristics for I/O pads when in FAST configuration.

Table 17. I/O pull-up/pull-down DC electrical characteristics

Symbol		C	Parameter	Conditions(1)		Value Min	Value Typ	Value Max	Unit
$\|I_{WPU}\|$	CC	P	Weak pull-up current absolute value	$V_{IN} = V_{IL}$, V_{DD} = 5.0 V ± 10%	PAD3V5V = 0	10	—	150	µA
		C			PAD3V5V = 1(2)	10	—	250	
		P		$V_{IN} = V_{IL}$, V_{DD} = 3.3 V ± 10%	PAD3V5V = 1	10	—	150	
$\|I_{WPD}\|$	CC	P	Weak pull-down current absolute value	$V_{IN} = V_{IH}$, V_{DD} = 5.0 V ± 10%	PAD3V5V = 0	10	—	150	µA
		C			PAD3V5V = 1	10	—	250	
		P		$V_{IN} = V_{IH}$, V_{DD} = 3.3 V ± 10%	PAD3V5V = 1	10	—	150	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

Table 18. SLOW configuration output buffer electrical characteristics

Symbol		C	Parameter	Conditions(1)		Value Min	Value Typ	Value Max	Unit
V_{OH}	CC	P	Output high level SLOW configuration	Push Pull	I_{OH} = –2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	$0.8V_{DD}$	—	—	V
		C			I_{OH} = –2 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1(2)	$0.8V_{DD}$	—	—	
		C			I_{OH} = –1 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	V_{DD}–0.8	—	—	

Table 24. I/O weight[1] (continued)

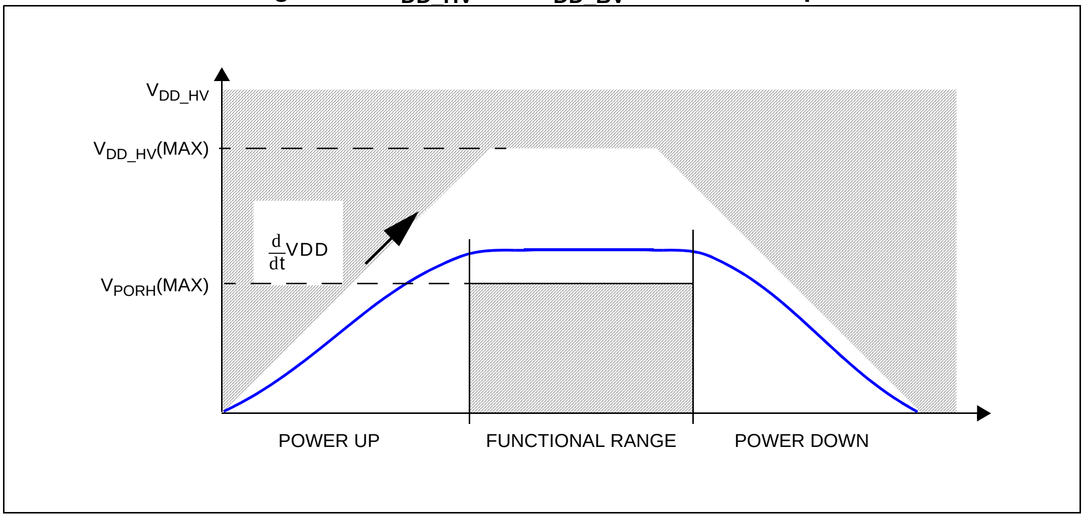
Supply segment			Pad	LQFP144/LQFP100				LQFP64[2]			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
LQFP 144	LQFP 100	LQFP 64		SRC[3] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
	—	—	PG[9]	9%	—	10%	—	—	—	—	—
	—	—	PG[8]	9%	—	11%	—	—	—	—	—
	1	—	PC[11]	9%	—	11%	—	—	—	—	—
		1	PC[10]	9%	13%	11%	12%	9%	13%	11%	12%
	—	—	PG[7]	10%	14%	11%	12%	—	—	—	—
	—	—	PG[6]	10%	14%	12%	12%	—	—	—	—
	1	1	PB[0]	10%	14%	12%	12%	10%	14%	12%	12%
			PB[1]	10%	—	12%	—	10%	—	12%	—
	—	—	PF[9]	10%	—	12%	—	—	—	—	—
	—	—	PF[8]	10%	15%	12%	13%	—	—	—	—
1	—	—	PF[12]	10%	15%	12%	13%	—	—	—	—
	1	1	PC[6]	10%	—	12%	—	10%	—	12%	—
			PC[7]	10%	—	12%	—	10%	—	12%	—
	—	—	PF[10]	10%	14%	12%	12%	—	—	—	—
	—	—	PF[11]	10%	—	11%	—	—	—	—	—
	1	1	PA[15]	9%	12%	10%	11%	9%	12%	10%	11%
	—	—	PF[13]	8%	—	10%	—	—	—	—	—
	1	1	PA[14]	8%	11%	9%	10%	8%	11%	9%	10%
			PA[4]	8%	—	9%	—	8%	—	9%	—
			PA[13]	7%	10%	9%	9%	7%	10%	9%	9%
			PA[12]	7%	—	8%	—	7%	—	8%	—

Table 25. Reset electrical characteristics (continued)

Symbol		C	Parameter	Conditions(1)	Value			Unit
					Min	Typ	Max	
V_{HYS}	CC	C	Input hysteresis CMOS (Schmitt Trigger)	—	$0.1V_{DD}$	—	—	V
V_{OL}	CC	P	Output low level	Push Pull, I_{OL} = 2mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 (recommended)	—	—	$0.1V_{DD}$	V
		C		Push Pull, I_{OL} = 1mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1(2)	—	—	$0.1V_{DD}$	
		C		Push Pull, I_{OL} = 1mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	—	—	0.5	
t_{tr}	CC	D	Output transition time output pin(3)	C_L = 25pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	10	ns
				C_L = 50pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	20	
				C_L = 100pF, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	40	
				C_L = 25pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	12	
				C_L = 50pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	25	
				C_L = 100pF, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	40	
W_{FRST}	SR	P	$\overline{RESET}$ input filtered pulse	—	—	—	40	ns
W_{NFRST}	SR	P	$\overline{RESET}$ input not filtered pulse	—	1000	—	—	ns
$\|I_{WPU}\|$	CC	P	Weak pull-up current absolute value	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	10	—	150	µA
		D		V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	10	—	150	
		P		V_{DD} = 5.0 V ± 10%, PAD3V5V = 1(2)	10	—	250	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified
2. This transient configuration does not occurs when device is used in the V_{DD} = 3.3 V ± 10% range.
3. C_L includes device and package capacitance (C_{PKG} < 5 pF).

Figure 10. V_{DD_HV} and V_{DD_BV} maximum slope



When STANDBY mode is used, further constraints are applied to the both V_{DD_HV} and V_{DD_BV} in order to guarantee correct regulator function during STANDBY exit. This is described on *Figure 11*.

STANDBY regulator constraints should normally be guaranteed by implementing equivalent of CSTDBY capacitance on application board (capacitance and ESR typical values), but would actually depend on exact characteristics of application external regulator.

Figure 11. V_{DD_HV} and V_{DD_BV} supply constraints during STANDBY mode exit

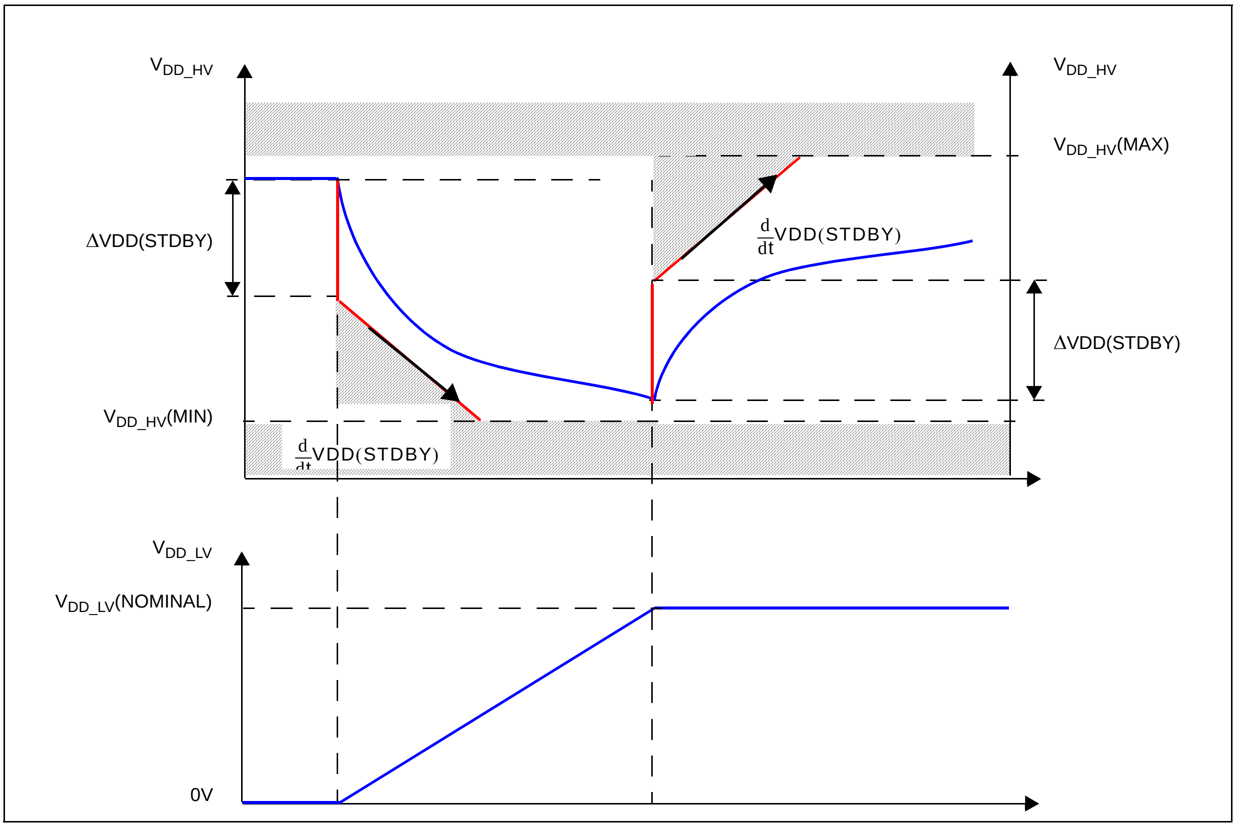


Table 26. Voltage regulator electrical characteristics

Symbol		C	Parameter	Conditions(1)	Value Min	Value Typ	Value Max	Unit
C_{REGn}	SR	—	Internal voltage regulator external capacitance	—	200	—	500	nF
R_{REG}	SR	—	Stability capacitor equivalent serial resistance	Range: 10 kHz to 20 MHz	—	—	0.2	W
C_{DEC1}	SR	—	Decoupling capacitance(2) ballast	V_{DD_BV}/V_{SS_LV} pair: V_{DD_BV} = 4.5 V to 5.5 V	100(3)	470(4)	—	nF
				V_{DD_BV}/V_{SS_LV} pair: V_{DD_BV} = 3 V to 3.6 V	400		—	
C_{DEC2}	SR	—	Decoupling capacitance regulator supply	V_{DD}/V_{SS} pair	10	100	—	nF
$\left\|\frac{d}{dt}VDD\right\|$	SR	—	Maximum slope on V_{DD}		—	—	250	mV/µs
$\|\Delta_{VDD(STDBY)}\|$	SR	—	Maximum instant variation on V_{DD} during standby exit		—	—	30	mV
$\left\|\frac{d}{dt}VDD(STDBY)\right\|$	SR	—	Maximum slope on V_{DD} during standby exit		—	—	15	mV/µs
V_{MREG}	CC	T	Main regulator output voltage	Before exiting from reset	—	1.32	—	V
		P		After trimming	1.16	1.28	—	
I_{MREG}	SR	—	Main regulator current provided to V_{DD_LV} domain	—	—	—	150	mA
$I_{MREGINT}$	CC	D	Main regulator module current consumption	I_{MREG} = 200 mA	—	—	2	mA
				I_{MREG} = 0 mA	—	—	1	
V_{LPREG}	CC	P	Low power regulator output voltage	After trimming	1.16	1.28	—	V
I_{LPREG}	SR	—	Low power regulator current provided to V_{DD_LV} domain	—	—	—	15	mA
$I_{LPREGINT}$	CC	D	Low power regulator module current consumption	I_{LPREG} = 15 mA; T_A = 55 °C	—	—	600	µA
		—		I_{LPREG} = 0 mA; T_A = 55 °C	—	5	—	
V_{ULPREG}	CC	P	Ultra low power regulator output voltage	After trimming	1.16	1.28	—	V

Table 26. Voltage regulator electrical characteristics (continued)

Symbol		C	Parameter	Conditions(1)	Value			Unit
					Min	Typ	Max	
I_{ULPREG}	SR	—	Ultra low power regulator current provided to V_{DD_LV} domain	—	—	—	5	mA
$I_{ULPREGINT}$	CC	D	Ultra low power regulator module current consumption	I_{ULPREG} = 5 mA; T_A = 55 °C	—	—	100	µA
				I_{ULPREG} = 0 mA; T_A = 55 °C	—	2	—	
I_{DD_BV}	CC	D	In-rush average current on V_{DD_BV} during power-up(5)	—	—	—	300 (6)	mA

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified
2. This capacitance value is driven by the constraints of the external voltage regulator supplying the V_{DD_BV} voltage. A typical value is in the range of 470 nF.
3. This value is acceptable to guarantee operation from 4.5 V to 5.5 V
4. External regulator and capacitance circuitry must be capable of providing I_{DD_BV} while maintaining supply V_{DD_BV} in operating range.
5. In-rush average current is seen only for short time (maximum 20 µs) during power-up and on standby exit. It is dependant on the sum of the C_{REGn} capacitances.
6. The duration of the in-rush current depends on the capacitance placed on LV pins. BV decoupling capacitors must be sized accordingly. Refer to I_{MREG} value for minimum amount of current to be provided in cc.

The $|\Delta_{VDD(STDBY)}|$ and dVDD(STDBY)/dt system requirement can be used to define the component used for the V_{DD} supply generation. The following two examples describe how to calculate capacitance size:

Example 1 No regulator (worst case)

The $|\Delta_{VDD(STDBY)}|$ parameter can be seen as the V_{DD} voltage drop through the ESR resistance of the regulator stability capacitor when the I_{DD_BV} current required to load V_{DD_LV} domain during the standby exit. It is thus possible to define the maximum equivalent resistance ESR_{STDBY}(MAX) of the total capacitance on the V_{DD} supply:

$ESR_{STDBY}(MAX) = |\Delta_{VDD(STDBY)}|/I_{DD\_BV} = (30\ mV)/(300\ mA) = 0.1\Omega$ [d]

The dVDD(STDBY)/dt parameter can be seen as the V_{DD} voltage drop at the capacitance pin (excluding ESR drop) while providing the I_{DD_BV} supply required to load V_{DD_LV} domain during the standby exit. It is thus possible to define the minimum equivalent capacitance C_{STDBY}(MIN) of the total capacitance on the V_{DD} supply:

$C_{STDBY}(MIN) = I_{DD\_BV}/dVDD(STDBY)/dt = (300\ mA)/(15\ mV/\mu s) = 20\ \mu F$

This configuration is a worst case, with the assumption no regulator is available.

Example 2 Simplified regulator

The regulator should be able to provide significant amount of the current during the standby exit process. For example, in case of an ideal voltage regulator providing 200 mA current, it is possible to recalculate the equivalent ESR_{STDBY}(MAX) and C_{STDBY}(MIN) as follows:

d. Based on typical time for standby exit sequence of 20 µs, ESR(MIN) can actually be considered at ~50 kHz.

released as soon as internal reset sequence is completed regardless of LVDHV5H threshold.

Table 27. Low voltage detector electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{PORUP}	SR	P	Supply for functional POR module	—	1.0	—	5.5	V
V_{PORH}	CC	P	Power-on reset threshold	T_A = 25 °C, after trimming	1.5	—	2.6	V
		T		—	1.5	—	2.6	V
$V_{LVDHV3H}$	CC	T	LVDHV3 low voltage detector high threshold	—	—	—	2.95	V
$V_{LVDHV3L}$	CC	P	LVDHV3 low voltage detector low threshold	—	2.6	—	2.9	V
$V_{LVDHV5H}$	CC	T	LVDHV5 low voltage detector high threshold	—	—	—	4.5	V
$V_{LVDHV5L}$	CC	P	LVDHV5 low voltage detector low threshold	—	3.8	—	4.4	V
$V_{LVDLVCORL}$	CC	P	LVDLVCOR low voltage detector low threshold	—	1.08	—	1.16	V
$V_{LVDLVBKPL}$	CC	P	LVDLVBKP low voltage detector low threshold	—	1.08	—	1.16	V

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

3.18 Power consumption

Table 28 provides DC electrical characteristics for significant application modes. These values are indicative values; actual consumption depends on the application.

Table 28. Power consumption on VDD_BV and VDD_HV

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
I_{DDMAX}[2]	CC	D	RUN mode maximum average current	—		—	115	140[3]	mA
I_{DDRUN}[4]	CC	T	RUN mode typical average current[5]	f_{CPU} = 8 MHz		—	7	—	mA
		T		f_{CPU} = 16 MHz		—	18	—	mA
		T		f_{CPU} = 32 MHz		—	29	—	mA
		P		f_{CPU} = 48 MHz		—	40	100	mA
		P		f_{CPU} = 64 MHz		—	51	125	mA
I_{DDHALT}	CC	C	HALT mode current[6]	Slow internal RC oscillator (128 kHz) running	T_A = 25 °C	—	8	15	mA
		P			T_A = 125 °C	—	14	25	mA

Table 31. Flash read access timing

Symbol		C	Parameter	Conditions(1)	Max	Unit
f_{READ}	CC	P	Maximum frequency for Flash reading	2 wait states	64	MHz
		C		1 wait state	40	
		C		0 wait states	20	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

3.19.2 Flash power supply DC characteristics

Table 32 shows the power supply DC characteristics on external supply.

Table 32. Flash memory power supply DC electrical characteristics

Symbol		C	Parameter	Conditions(1)	Value Min	Value Typ	Value Max	Unit
I_{FREAD} (2)	CC	D	Sum of the current consumption on VDD_HV and VDD_BV on read access	Code flash memory module read f_{CPU} = 64 MHz(3)	—	15	33	mA
				Data flash memory module read f_{CPU} = 64 MHz(3)	—	15	33	
I_{FMOD} (2)	CC	D	Sum of the current consumption on VDD_HV and VDD_BV on matrix modification (program/erase)	Program/Erase ongoing while reading code flash memory registers f_{CPU} = 64 MHz(3)	—	15	33	mA
				Program/Erase ongoing while reading data flash memory registers f_{CPU} = 64 MHz(3)	—	15	33	
I_{FLPW}	CC	D	Sum of the current consumption on VDD_HV and VDD_BV	During code flash memory low-power mode	—	—	900	µA
				During data flash memory low-power mode	—	—	900	
I_{FPWD}	CC	D	Sum of the current consumption on VDD_HV and VDD_BV	During code flash memory power-down mode	—	—	150	µA
				During data flash memory power-down mode	—	—	150	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified
2. This value is only relative to the actual duration of the read cycle
3. f_{CPU} 64 MHz can be achieved only at up to 105 °C

To preserve the accuracy of the A/D converter, it is necessary that analog input pins have low AC impedance. Placing a capacitor with good high frequency characteristics at the input pin of the device can be effective: the capacitor should be as large as possible, ideally infinite. This capacitor contributes to attenuating the noise present on the input pin; furthermore, it sources charge during the sampling phase, when the analog signal source is a high-impedance source.

A real filter can typically be obtained by using a series resistance with a capacitor on the input pin (simple RC filter). The RC filtering may be limited according to the value of source impedance of the transducer or circuit supplying the analog signal to be measured. The filter at the input pins must be designed taking into account the dynamic characteristics of the input signal (bandwidth) and the equivalent input impedance of the ADC itself.

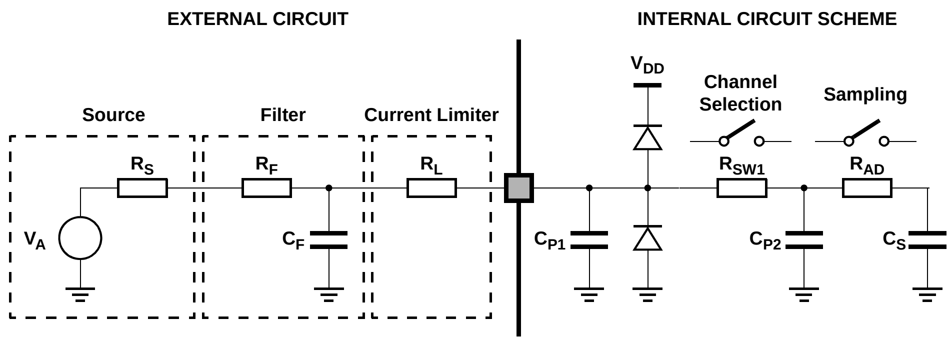
In fact a current sink contributor is represented by the charge sharing effects with the sampling capacitance: being C_S and C_{p2} substantially two switched capacitances, with a frequency equal to the conversion rate of the ADC, it can be seen as a resistive path to ground. For instance, assuming a conversion rate of 1 MHz, with C_S+C_{p2} equal to 3 pF, a resistance of 330 kΩ is obtained ($R_{EQ} = 1 / (f_c \times (C_S+C_{p2}))$, where f_c represents the conversion rate at the considered channel). To minimize the error induced by the voltage partitioning between this resistance (sampled voltage on C_S+C_{p2}) and the sum of R_S + R_F, the external circuit must be designed to respect the *Equation 4*:

Equation 4

$$V_A \bullet \frac{R_S + R_F}{R_{EQ}} < \frac{1}{2} LSB$$

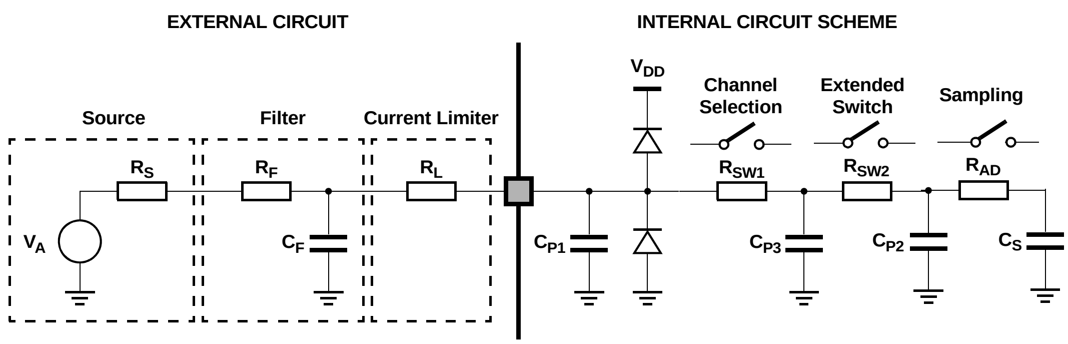
Equation 4 generates a constraint for external network design, in particular on a resistive path.

Figure 19. Input equivalent circuit (precise channels)



R_S: Source impedance
R_F: Filter resistance
C_F: Filter capacitance
R_L: Current limiter resistance
R_{SW1}: Channel selection switch impedance
R_{AD}: Sampling switch impedance
C_P: Pin capacitance (two contributions, C_{P1} and C_{P2})
C_S: Sampling capacitance

Figure 20. Input equivalent circuit (extended channels)



R_S: Source impedance
R_F: Filter resistance
C_F: Filter capacitance
R_L: Current limiter resistance
R_{SW1}: Channel selection switch impedance (two contributions, R_{SW1} and R_{SW2})
R_{AD}: Sampling switch impedance
C_P: Pin capacitance (two contributions, C_{P1}, C_{P2} and C_{P3})
C_S: Sampling capacitance

Table 45. ADC conversion characteristics (continued)

Symbol		C	Parameter	Conditions[(1)]		Value			Unit
						Min	Typ	Max	
I_{INJ}	SR	—	Input current Injection	Current injection on one ADC input, different from the converted one	V_{DD} = 3.3 V ± 10%	–5	—	5	mA
					V_{DD} = 5.0 V ± 10%	–5	—	5	
| INL |	CC	T	Absolute value for integral non-linearity	No overload		—	0.5	1.5	LSB
| DNL |	CC	T	Absolute differential non-linearity	No overload		—	0.5	1.0	LSB
| E_O |	CC	T	Absolute offset error	—		—	0.5	—	LSB
| E_G |	CC	T	Absolute gain error	—		—	0.6	—	LSB
TUEp	CC	P	Total unadjusted error[(7)] for precise channels, input only pins	Without current injection		–2	0.6	2	LSB
		T		With current injection		–3		3	
TUEx	CC	T	Total unadjusted error[(7)] for extended channel	Without current injection		–3	1	3	LSB
		T		With current injection		–4		4	

1. V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2. Analog and digital V_{SS} **must** be common (to be tied together externally).
3. V_{AINx} may exceed V_{SS_ADC} and V_{DD_ADC} limits, remaining on absolute maximum ratings, but the results of the conversion will be clamped respectively to 0x000 or 0x3FF.
4. Duty cycle is ensured by using system clock without prescaling. When ADCLKSEL = 0, the duty cycle is ensured by internal divider by 2.
5. During the sampling time the input capacitance C_S can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_s. After the end of the sampling time t_s, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_s depend on programming.
6. This parameter does not include the sampling time t_s, but only the time for determining the digital result and the time to load the result's register with the conversion result.
7. Total Unadjusted Error: The maximum error that occurs without adjusting Offset and Gain errors. This error is a combination of Offset, Gain and Integral Linearity errors.

3.27 On-chip peripherals

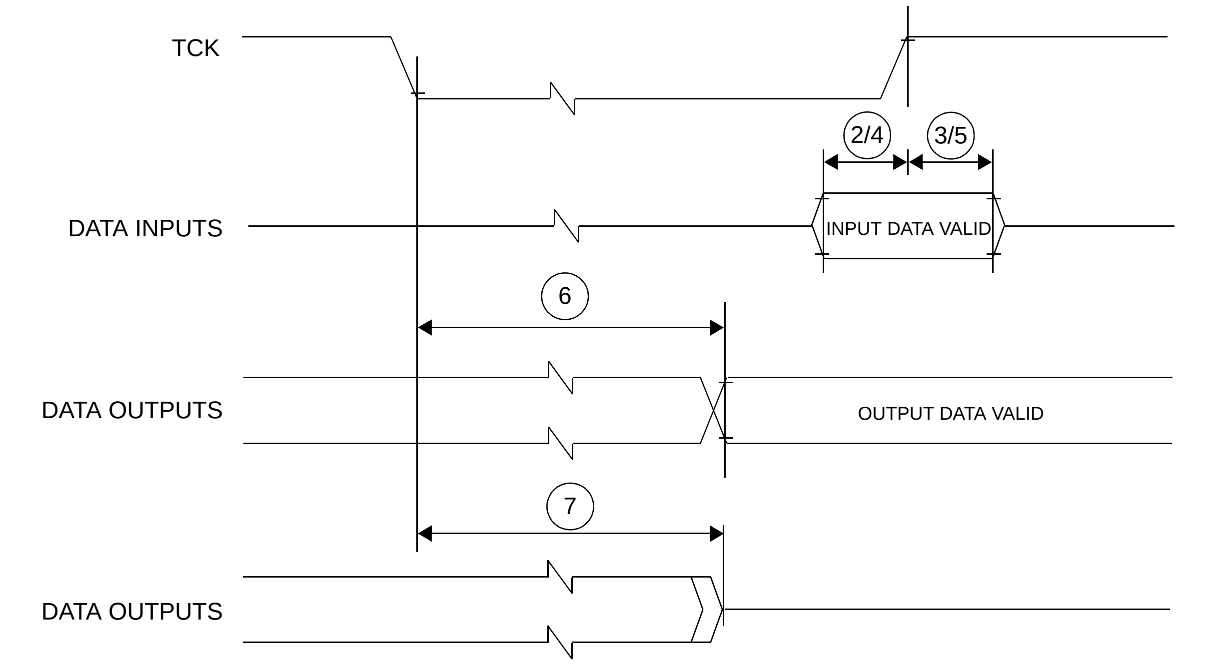
3.27.1 Current consumption

3.27.4 JTAG characteristics

Table 49. JTAG characteristics

No.	Symbol		C	Parameter	Value			Unit
					Min	Typ	Max	
1	t_{JCYC}	CC	D	TCK cycle time	64	—	—	ns
2	t_{TDIS}	CC	D	TDI setup time	15	—	—	ns
3	t_{TDIH}	CC	D	TDI hold time	5	—	—	ns
4	t_{TMSS}	CC	D	TMS setup time	15	—	—	ns
5	t_{TMSH}	CC	D	TMS hold time	5	—	—	ns
6	t_{TDOV}	CC	D	TCK low to TDO valid	—	—	33	ns
7	t_{TDOI}	CC	D	TCK low to TDO invalid	6	—	—	ns

Figure 33. Timing diagram – JTAG boundary scan



Note: Numbers shown reference *Table 49*.

Table 55. Document revision history (continued)

Date	Revision	Changes
18-Jan-2013	11	In the cover feature list, replaced “System watchdog timer” with “Software watchdog timer” *Table 3 (SPC560B40x/50x and SPC560C40x/50x series block summary)*, replaced “System watchdog timer” with “Software watchdog timer” and specified AUTOSAR (Automotive Open System Architecture) *Table 6 (Functional port pin descriptions)*, replaced VDD with VDD_HV *Figure 9 (Voltage regulator capacitance connection)*, updated pin name apperence Renamed *Figure 10 (V_{DD_HV} and V_{DD_BV} maximum slope)* (was “VDD and VDD_BV maximum slope”) and replaced VDD_HV(MIN) with VPORH(MAX) Renamed *Figure 11 (V_{DD_HV} and V_{DD_BV} supply constraints during STANDBY mode exit)* (was “VDD and VDD_BV supply constraints during STANDBY mode exit”) *Table 13 (Recommended operating conditions (3.3 V))*, added minimum value of T_{VDD} and footnote about it. *Table 14 (Recommended operating conditions (5.0 V))*, added minimum value of T_{VDD} and footnote about it. *Section 3.17.1, Voltage regulator electrical characteristics*: replaced “slew rate of V_{DD}/V_{DD_BV}” with “slew rate of both V_{DD_HV} and V_{DD_BV}” replaced “When STANDBY mode is used, further constraints apply to the V_{DD}/V_{DD_BV} in order to guarantee correct regulator functionality during STANDBY exit.” with “When STANDBY mode is used, further constraints are applied to the both V_{DD_HV} and V_{DD_BV} in order to guarantee correct regulator function during STANDBY exit.” *Table 28 (Power consumption on VDD_BV and VDD_HV)*, updated footnotes of I_{DDMAX} and I_{DDRUN} stating that both currents are drawn only from the V_{DD_BV} pin. *Table 32 (Flash memory power supply DC electrical characteristics)*, in the paremeter column replaced V_{DD_BV} and V_{DD_HV} respectively with VDD_BV and VDD_HV. *Table 46 (On-chip peripherals current consumption)*, in the paremeter column replaced V_{DD_BV}, V_{DD_HV} and $V_{DD\_HV\_ADC}$ respectively with VDD_BV, VDD_HV and VDD_HV_ADC Updated *Section 3.26.2, Input impedance and ADC accuracy* *Table 47 (DSPI characteristics)*, modified symbol for t_{PCSC} and t_{PASC}
18-Sep-2013	12	Updated Disclaimer.
03-Feb-2015	13	In *Table 2: SPC560B40x/50x and SPC560C40x/50x device comparison*: – changed the MPC5604BxLH entry for CAN (FlexCAN) from 3[7] to 2[6]. – updated tablenote 7. In *Table 14: Recommended operating conditions (5.0 V)*, updated tablenote 5 to: “1 µF (electrolithic/tantalum) + 47 nF (ceramic) capacitance needs to be provided between V_{DD_ADC}/V_{SS_ADC} pair. Another ceramic cap of 10nF with low inductance package can be added”. In *Section 3.17.2: Low voltage detector electrical characteristics*, added a note on LVHVD5 detector. In *Section 5: Ordering information*, added a note: “Not all options are available on all devices”.